LDMOS 3-stage integrated Doherty MMIC Rev. 1 — 30 January 2023

Product profile 1.

1.1 General description

The B11G3742N81D is a dual section 3-stage fully integrated Doherty MMIC solution using Ampleon's state of the art LDMOS technology. The carrier and peaking device, input splitter, output combiner and pre-match are integrated in each section. This multiband device is perfectly suited as general purpose driver in the frequency range 3700 MHz to 4200 MHz. Available in PQFN outline.

Table 1. **Application performance**

Typical RF performance at $T_{case} = 25 \ ^{\circ}C$; $I_{Dq} = 210 \ mA$ (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.55$ V. Test signal: 1-carrier LTE 20 MHz; PAR = 7.6 dB measured in an Ampleon f = 4000 MHz integrated Doherty combined application circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	ηם
	(MHz)	(V)	(W)	(dB)	(%)
1-carrier LTE 20 MHz PAR = 7.6 dB	4000	28	5	31.7	20.2

1.2 Features and benefits

- Integrated input splitter
- Integrated output combiner
- 20 Ω output impedance thanks to integrated pre-match
- High linearity
- Designed for large RF and instantaneous bandwidth operation
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Integrated bias gate switch
- Source impedance 50 Ω ; high power gain
- For RoHS compliance see the product details on the Ampleon website

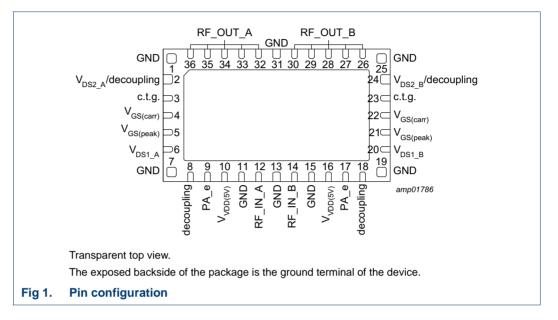
1.3 Applications

- Macrocell base station driver
- Microcell base station
- 5G mMIMO
- W-CDMA/LTE
- Active antenna
- General purpose applications

LDMOS 3-stage integrated Doherty MMIC

2. Pinning information

2.1 Pinning



2.2 Pin description

Symbol	Pin	Description
GND	1	ground
V _{DS2_A} /decoupling	2	drain-source voltage of final stages of section A ^[1]
c.t.g.	3	connect to ground
V _{GS(carr)}	4	gate-source voltage of carrier [2]
V _{GS(peak)}	5	gate-source voltage of peaking 3
V _{DS1_A}	6	drain-source voltage of driver stages of section A
GND	7	ground
decoupling	8	video-lead for decoupling [1]
PA_e	9	PA enable trigger signal, 0 V to 5 V, I _{Dq} -bias ON/OFF corresponds to logic HIGH/LOW [4]
V _{DD(5V)}	10	supply voltage (5 V) 5
GND	11	ground
RF_IN_A	12	RF input of section A
GND	13	ground
RF_IN_B	14	RF input of section B
GND	15	ground
V _{DD(5V)}	16	supply voltage (5 V) 5
PA_e	17	PA enable trigger signal, 0 V to 5 V, I _{Dq} -bias ON/OFF corresponds to logic HIGH/LOW [4]
decoupling	18	video-lead for decoupling [6]

Table 2. Pin description

All information provided in this document is subject to legal disclaimers.

Symbol	Pin	Description		
GND	19	ground		
V _{DS1_B}	20	drain-source voltage of driver stages of section B		
V _{GS(peak)}	21	gate-source voltage of peaking 3		
V _{GS(carr)}	22	gate-source voltage of carrier [2]		
c.t.g.	23	connect to ground		
V _{DS2_B} /decoupling	24	drain-source voltage of final stages of section B 6		
GND	25	ground		
RF_OUT_B	26, 27, 28, 29, 30	RF output of section B		
GND	31	ground		
RF_OUT_A	32, 33, 34, 35, 36	RF output of section A		

- [1] Pins connected together.
- [2] Pins connected together.
- [3] Pins connected together.
- [4] Pins connected together.
- [5] Pins connected together.
- [6] Pins connected together.

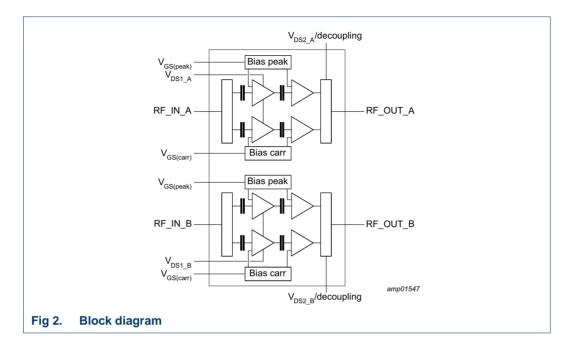
3. Ordering information

Table 3. Ordering information

Package name	Orderable part number	12NC	Packing description	Min. orderable quantity (pieces)
PQFN-12x7-36-1	B11G3742N81DX	9349 606 59525	TR13; 1500-fold; 24 mm; dry pack	1500
	B11G3742N81DYZ	9349 606 59535	TR7; 300-fold; 24 mm; dry pack	300

LDMOS 3-stage integrated Doherty MMIC

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage		-	65	V
V _{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	<u>[1]</u>	-	200	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Measured for total device.

Symbol	Parameter	Conditions		Value	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 90 \ ^{\circ}C$			
		$P_L = 5 W$	[1]	1.5	K/W
		P _L = 10 W	<u>[1]</u>	1.2	K/W

[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

LDMOS 3-stage integrated Doherty MMIC

7. Characteristics

Table 6. DC characteristics

 $T_{case} = 25 \ ^{\circ}C; \ V_{DD(5V)} = 5 \ V; \ V_{on(PA_e)} = 5 \ V.$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Carrier	l					
V _{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 195 \text{ mA}$	1.7	2.0	2.4	V
I _{GSS}	gate leakage current	$V_{GS} = 2 V; V_{DS} = 0 V$	-	-	140	nA
Peaking	1					
I _{GSS}	gate leakage current	$V_{GS} = 2 V; V_{DS} = 0 V$	-	-	140	nA
Final sta	ges					
I _{DSS}	drain leakage current	$V_{GS} = 0 V; V_{DS} = 28 V$	-	-	1.4	μA
Driver st	ages					
I _{DSS}	drain leakage current	$V_{GS} = 0 V; V_{DS} = 28 V$	-	-	1.4	μA

Table 7.RF characteristics

Typical RF performance at $T_{case} = 25 \, ^{\circ}C$; $V_{DS} = 28 \, V$; $I_{Dq} = 195 \, mA$ (carrier); $f = 3950 \, MHz$; $V_{DD(5V)} = 4.8 \, V$; $V_{on(PA_e)} = 5 \, V$; $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.55 \, V$; $P_{L(AV)} = 5 \, W$; unless otherwise specified, measured in an Ampleon combined production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Test sigr	nal: pulsed CW [1]					
G _p	power gain	P _L = 5 W (37 dBm)	29.5	32	36	dB
η_D	drain efficiency	P _L = 5 W (37 dBm)	14	20	-	%
		$P_L = P_{L(3dB)}$	30	38	-	%
RL _{in}	input return loss	P _L = 5 W (37 dBm)	-	-15	-10	dB
P _{L(3dB)}	output power at 3 dB gain compression	$P_L = P_L(3dB)$	47.5	48.5	-	dBm

[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 µs).

8. Application information

8.1 Typical performance

Table 8. Typical performance

 $T_{case} = 25 \text{ °C}; V_{DS} = 28 \text{ V}; I_{Dq} = 210 \text{ mA} \text{ (carrier and peaking)}; V_{GSq(peaking)} = V_{GSq(carrier)} - 0.55 \text{ V}; V_{DD(5V)} = 5 \text{ V}; V_{on(PA_e)} = 5 \text{ V}.$ Test signal: 1-carrier W-CDMA; PAR = 9.9 dB; unless otherwise specified, measured in an Ampleon 3700 MHz to 4200 MHz frequency band combined application circuit.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P _{L(1dB)}	output power at 1 dB gain compression	f = 4000 MHz	[1]	-	48.4	-	dBm
$\phi_{s21}/\phi_{s21}(norm)$	normalized phase response	at 1 dB compression point; f = 4000 MHz	[2]	-	-11.3	-	0
η _D	drain efficiency	12 dB OBO (P _{L(AV)} = 37 dBm); f = 4000 MHz		-	20.3	-	%
G _p	power gain	P _{L(AV)} = 37 dBm; f = 4000 MHz		-	31.7	-	dB
B _{video}	video bandwidth	$P_{L(AV)} = 37 \text{ dBm set to obtain}$ IMD3 = -45 dBc; 2-tone CW; f = 4000 MHz		-	400	-	MHz
G _{flat}	gain flatness	P _{L(AV)} = 37 dBm; f = 3700 MHz to 4200 MHz		-	0.9	-	dB
ACPR _{5M}	adjacent channel power ratio (5 MHz)	P _{L(AV)} = 37 dBm; f = 4000 MHz		-	-38.3	-	dBc
$\Delta G / \Delta T$	gain variation with temperature	f = 4000 MHz		-	0.06	-	dB/∘C
К	Rollett stability factor	$T_{case} = -40$ °C to +125 °C; f = 0.1 GHz to 8 GHz		-	>1	-	
Bias gate swi	tch				1		
t _r	rise time	$ Z_{S} = 500 \ \Omega \ (max); T_{case} = -40 \ ^{\circ}C \ to $	<u>[3]</u>	-	200	-	ns
t _f	fall time	$ T_{case} = -40 \ ^{\circ}C \ to \ +120 \ ^{\circ}C; $	[4]	-	80	-	ns

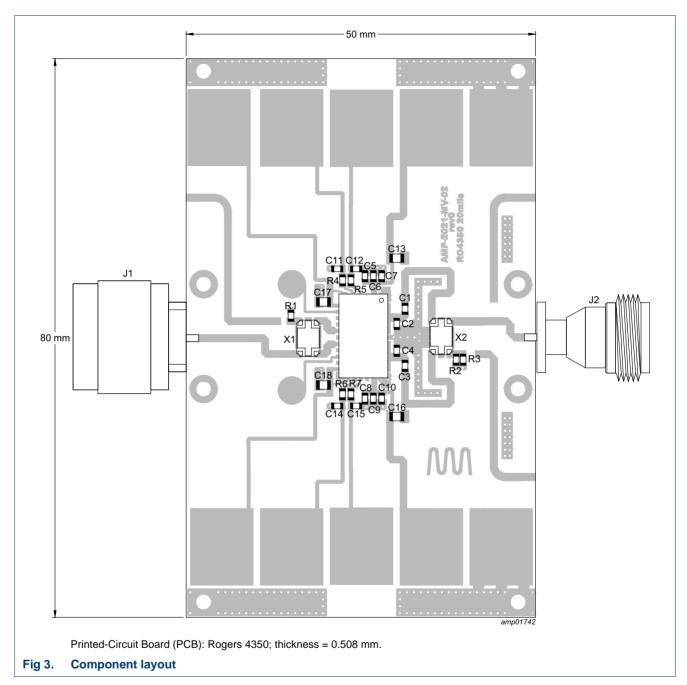
[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 µs).

[2] 25 ms CW power sweep measurement.

[3] RF output rise time 10 % to 90 % RF power.

[4] RF output fall time 90 % to 10 % RF power.

LDMOS 3-stage integrated Doherty MMIC



8.2 PCB layout and electrical schematic

Table 9.List of componentsSee Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C3	multilayer ceramic chip capacitor	3.9 pF, ± 0.1 %	Murata: GQM1875C2E3R9BB12
C2, C4	multilayer ceramic chip capacitor	0.2 pF, ± 0.1 %	Murata: GQM1875C2E0R2BB12
C5, C6, C7, C8, C9, C10	multilayer ceramic chip capacitor	100 nF, 50 V	Murata: 06035C104KAT2A

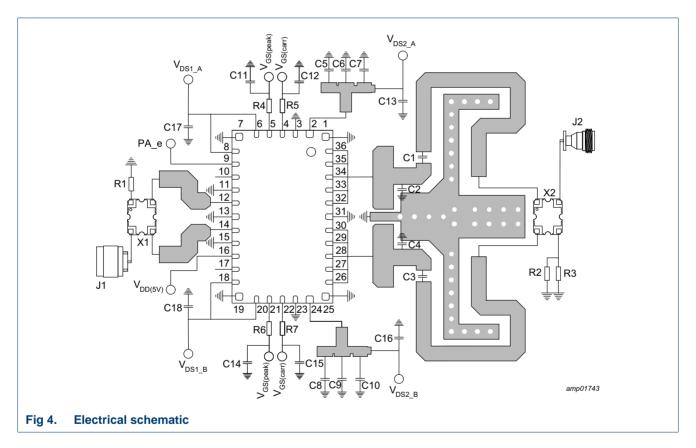
B11G3742N81D

LDMOS 3-stage integrated Doherty MMIC

Table 9. List of components ...continued

See Figure 3 for component layout.

Component	Description	Value	Remarks
C11, C12, C14, C15	multilayer ceramic chip capacitor	1 μF, 50 V	Murata: C1608X5R1H105K080AB
C13, C16, C17, C18	multilayer ceramic chip capacitor	10 μF, 50 V	Murata: GRM21BR6YA106KE43
R1	resistor	49.9 Ω , ± 1 %, 100 mW	Multicomp Pro: MCWF06R49R9BTL
R2, R3	resistor	100 Ω , ± 1 %, 200 mW	Multicomp Pro: MP001293
R4, R5, R6, R7	resistor	1 k Ω , \pm 1 %, 100 mW	Multicomp Pro: MCSR06X1001FTL
X1, X2	hybrid coupler	3.7 GHz – 4.2 GHz, 25 W	Anaren: X3C45F1-03S
J1	N Coaxial panel connector male		Radiall: R161.438.200
J2	N Coaxial panel connector female		Huber & Suhner: 23_N-50-0-16/133_NE



8.3 Recommendations

- RC circuit at gate bias must be implemented to insure improved linearity and stability of the circuit. The implementation has to be symmetrical between both amplifier sections Pin 5/21 and Pin 4/22.
- In TDD mode controlled by an external bias switch, the outputs of the switches must be connected on both amplifier sections. As shown in Fig.4, gate bias supply must be connected before RC circuit of Pin 5/21 and Pin 4/22 respectively by default.

8.4 Ruggedness in a Doherty operation

8.4.1 Output mismatch ruggedness

The B11G3742N81D is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 32$ V; $I_{Dq} = 110$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.55$ V; $V_{DD(5V)} = 5$ V; $V_{on(PA_e)} = 5$ V; P_i corresponding to $P_{L(3dB)} - 9$ dB under $Z_S = 50 \Omega$ load; f = 4200 MHz (1-carrier W-CDMA); $T_{case} = 25$ °C; per section.

8.4.2 Wideband noise ruggedness

The B11G3742N81D is capable of withstanding an AWGN (Additive White Gaussian Noise) with 11.2 dB PAR, OBW (Occupied BandWidth) of 900 MHz, under the following conditions: $V_{DS} = 32$ V; $I_{Dq} = 110$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.55$ V; $V_{DD(5V)} = 5$ V; $V_{on(PA_e)} = 5$ V; 3 dB P_i overdrive from $P_{L(AV)} = 34$ dBm (corresponding to $P_{L(3dB)} - 12$ dB); f = 3950 MHz as central frequency; $T_{case} = 25$ °C; per section.

8.5 Impedance information

Table 10. Typical impedance for optimum Doherty operation

Measured load-pull data per section; test signal: pulsed CW; $T_{case} = 25 \text{ °C}$; $V_{DS} = 28 \text{ V}$; $I_{Dq} = 110 \text{ mA}$ (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.55 \text{ V}$; $V_{DD(5V)} = 5 \text{ V}$; $V_{on(PA_e)} = 5 \text{ V}$; $t_p = 100 \ \mu\text{s}$; $\delta = 10 \ \%$.

	tuned for optimum Doherty operation				
f	Z _L [1]	P _{L(1dB)}	G _{p(max)}	η _{add} [2]	໗add <mark>[3]</mark>
(MHz)	(Ω)	(dBm)	(dB)	(%)	(%)
3600	22.2 – j18.85	46.0	34.1	44.7	23.3
3700	23.8 – j17.70	46.0	33.9	44.3	23.7
3800	22.1 – j16.00	46.0	34.0	44.5	23.5
3900	20.1 – j16.80	46.1	34.3	45.3	22.9
4000	20.0 – j16.90	46.1	34.3	45.5	22.4
4100	19.2 – j19.30	46.2	34.2	46.1	21.7
4200	18.8 – j19.90	46.1	34.0	45.9	21.4
4300	18.8 – j20.00	45.8	33.8	44.8	20.9

[1] Reference package plane.

[2] At P_{L(1dB)}.

[3] At 34 dBm.

LDMOS 3-stage integrated Doherty MMIC

9. Package outline

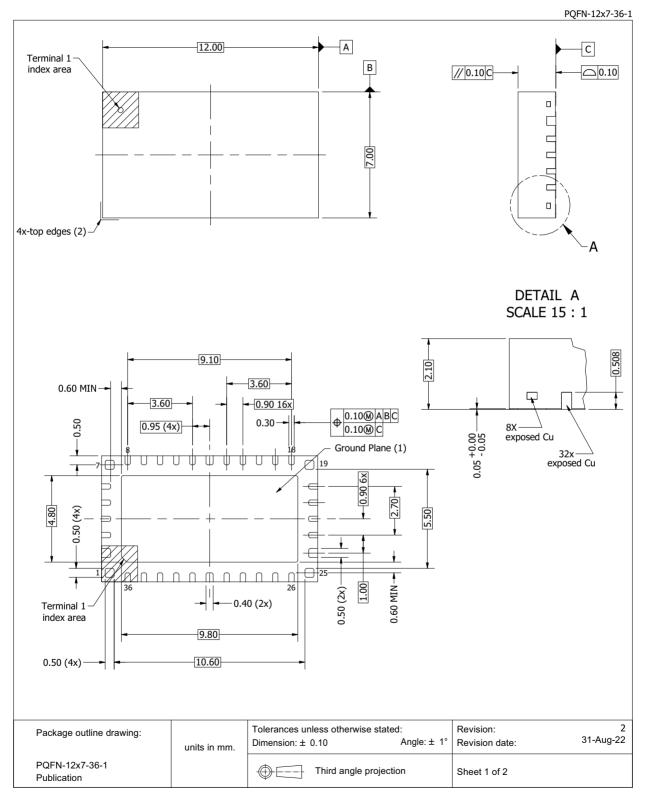


Fig 5. Package outline PQFN-12x7-36-1 (sheet 1 of 2)

B11G3742N81D

All information provided in this document is subject to legal disclaimers

LDMOS 3-stage integrated Doherty MMIC

PQFN-12x7-36-1

			Drawing Notes	
Items			Description	
(1)			tom View) are plated with matte Sn.	
(2)	Plastic protrusions of 0.07	75 mm. max. per s	ide are not included.	
				1
		1	Tolerances unless otherwise stated:	Revision:
Pack	age outline drawing:			
Pack	age outline drawing:	units in mm	Dimension: ± 0.10 Angle: ± 1°	Revision date: 31-Au
		units in mm.		
PQFI	age outline drawing: N-12x7-36-1 cation	units in mm.		

Fig 6. Package outline PQFN-12x7-36-1 (sheet 2 of 2)

B11G3742N81D

LDMOS 3-stage integrated Doherty MMIC

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11.ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C1 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1C [2]

[1] CDM classification C1 is granted to any part that passes after exposure to an ESD pulse of 250 V.

[2] HBM classification 1C is granted to any part that passes after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 12. Abbreviations			
Acronym	Description		
5G	Fifth Generation		
CW	Continuous Wave		
ESD	ElectroStatic Discharge		
LDMOS	Laterally Diffused Metal Oxide Semiconductor		
LTE	Long Term Evolution		
MMIC	Monolithic Microwave Integrated Circuit		
mMIMO	massive Multiple Input Multiple Output		
MTF	Median Time to Failure		
OBO	Output Back Off		
PA	Power Amplifier		
PAR	Peak-to-Average power Ratio		
RC	resistor-capacitor		
RoHS	Restriction of Hazardous Substances		
TDD	Time Division Duplex		
VSWR	Voltage Standing Wave Ratio		
W-CDMA	Wideband Code Division Multiple Access		

12. Revision history

Table 13.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
B11G3742N81D v.1	20230130	Product data sheet	-	-

B11G3742N81D

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Ampleon does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Ampleon sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Ampleon and its customer, unless Ampleon and customer have explicitly agreed otherwise in writing. An agreement according to which the functions and qualities of Ampleon products exceed those described in the Product data sheet is invalid.

13.3 Disclaimers

Maturity — After the relevant product(s) have passed the Release Gate in Ampleon's release process, Ampleon will confirm the final version in writing.

Limited warranty and liability — Ampleon uses its best efforts to keep the information in this document accurate and reliable. However, Ampleon gives no representations or warranties, expressed or implied, as to the accuracy or completeness of such information and assumes no liability for the consequences of the use of such information. Ampleon is not liable for content provided by an external information source.

In no event and irrespective of the legal basis (contract, tort (including negligence) statutory liability, misrepresentation, indemnity or any other area of law) shall Ampleon be liable for any indirect, incidental, punitive, special or consequential damages (including but without limitation loss of profit or revenue, loss of use or loss of production, loss of data, cost of capital, cost of substitute goods, property damage external to the Ampleon products and any damage, expenditure or loss arising out of such damage, business interruption, costs related to the removal or replacement of any products or rework charges) or any of the foregoing suffered by any third party.

Notwithstanding any damages that customer might incur for any reason whatsoever, Ampleon's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Ampleon.

Right to make changes — Ampleon reserves the right to change information including but without limitation specifications and product descriptions published in this document at any time and without notice. This document supersedes and replaces all information regarding these products supplied prior to the publication hereof.

Suitability for use — Ampleon products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an Ampleon product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Insofar as a customer or another party nevertheless uses Ampleon products unlawfully for such purposes. Ampleon and its suppliers are not liable for any damages.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Ampleon makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Ampleon products, and Ampleon is not liable for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Ampleon product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers shall provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Ampleon is not liable related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for and shall do all necessary testing for the customer's applications and products using Ampleon products in order to avoid a default of the applications and the products or of the application or use by customer's. Ampleon is not liable in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not guaranteed. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Ampleon products are sold subject to the general terms and conditions of commercial sale, as published at http://www.ampleon.com/terms, unless otherwise agreed in a valid written individual agreement. In the event of signing an individual agreement the terms and conditions of the respective agreement shall apply. Ampleon hereby expressly objects to and rejects the validity of customer's terms and conditions regarding the purchase of Ampleon products by customer.

LDMOS 3-stage integrated Doherty MMIC

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific Ampleon product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Ampleon is not liable for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer breaches this and uses the products for design and use in automotive applications in accordance with automotive specifications and standards, (a) Ampleon gives no warranty, representation

14. Contact information

or other guarantees of any kind with respect to such automotive applications, use and specifications, and (b) such use is solely and exclusively at customer's own risk, and (c) customer fully indemnifies Ampleon against any and all liability, damages or failed product claims, including against third parties, arising out of customer's design and use of the product for automotive applications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

LDMOS 3-stage integrated Doherty MMIC

15. Contents

15	Contents 1	5
14		4
13.4		4
13.3		3
13.2		3
13.1		3
13		3
12	······································	2
11		2
10		2
9	Package outline	
		-
8.4.2 8.5	Wideband noise ruggedness	9 9
8.4.1	Output mismatch ruggedness	9
8.4	Ruggedness in a Doherty operation	9
8.3	Recommendations	8
8.2	PCB layout and electrical schematic	7
8.1	Typical performance	6
8	Application information	6
7	Characteristics	5
6	Thermal characteristics	4
5	Limiting values	4
4	Block diagram	4
3	Ordering information	3
2.2	Pin description	2
2.1	Pinning	2
2	Pinning information	
1.3	Applications	1
1.2	Features and benefits	1
1.1	General description	
1	Product profile	

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© Ampleon Netherlands B.V. 2023.

All rights reserved.

For more information, please visit: http://www.ampleon.com For sales office addresses, please visit: http://www.ampleon.com/sales

Date of release: 30 January 2023 Document identifier: B11G3742N81D